정렬된 다공질 산화알루미늄을 이용한 새로운 다결정 실리콘 결정화 방법

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Novel Method of Poly-silicon Crystallization using Ordered Porous Anodic Alumina

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Abstract: Highly ordered pore structures as a template for formation of seeds have been prepared by the self-organization process of aluminum oxidation. The a-Si films were deposited on the anodic alumina films and crystallized by laser irradiation. It was found that un-melted part of fine poly-Si grain formed by explosive crystallization (EX) lead super lateral growth (SLG) and occluded with neighbor grains. The crystallized grains along the distribution of seeds were obtained. This results show a great potential for use in novel crystallization for decently uniform polycrystalline Si thin film transistors (poly-Si TFTs).

Key Words: anodic alumina, crystallization, poly-silicon, excimer laser